

HD153009, HD153013

2-7 Code Encoder/Decoder

Description

The HD153009/HD153013 2-7 encoder/decoder IC for magnetic disks converts an NRZ signal to be written to a magnetic disk into a 2-7 code, and converts a 2-7 code read from the disk into an NRZ signal.

This IC incorporates phase comparator logic for the data separator. In combination with a data separator chip, this IC performs two functions: 2-7 modulation/demodulation and data separation.

Features

- Encode/decode IBM 2-7 codes
- Can generate and detect address marks using soft sector approach.
- Can synchronize phases in 4T (1000) SYNC pattern.
- Built-in phase comparison logic for data separation
- Built-in sync field detection logic
- Maximum data transfer rate: 15 Mbps
- LSTTL-compatible inputs/outputs
- Small 44-pin MSP package suitable for surface mounting
- Single 5 V power supply

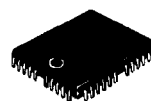
Functions

- NRZ signal to 2-7 code conversion
- 2-7 code to NRZ signal conversion
- Write precompensation
- Phase synchronization in 4T(1000) SYNC pattern
- Address mark(DC erase) generation
- Address mark(DC erase) detection
- Phase comparison for data separator
- Sync field detection

Ordering Information

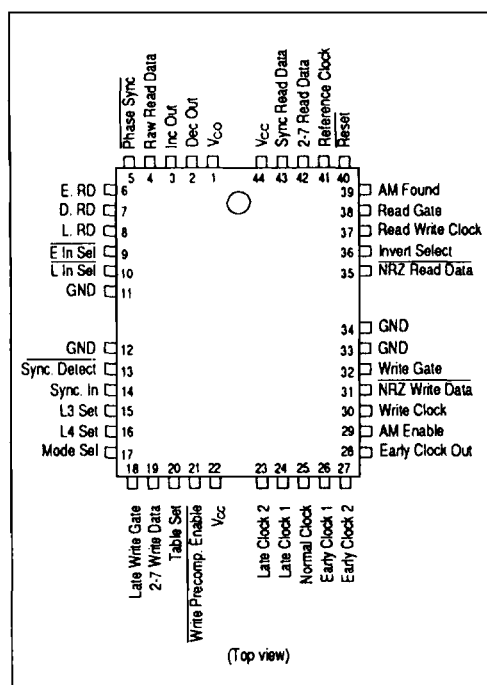
Type No.	Package
HD153009, HD153013	MP-44

HD153009, HD153013



(MP-44)

Pin Arrangement



Block Diagram

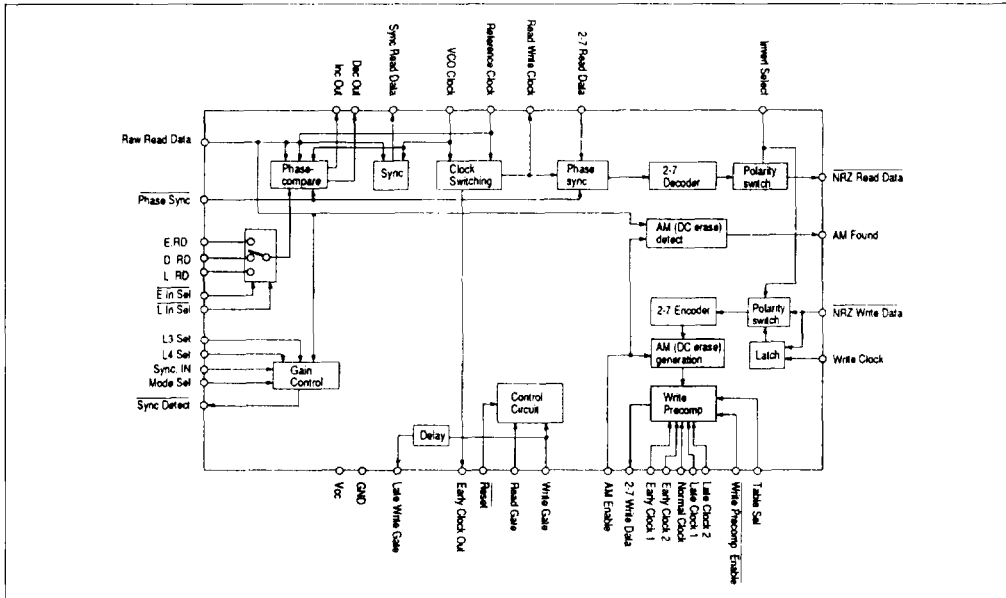


Table 1 Pin Description

Pin No.	Pin name	Input/output
22,24	Vcc	Power
11,12,33,34	GND	Power
42	2-7 Read data	In
1	VCO clock	In
38	Read gate	In
41	Reference clock	In
31	NRZ write data	In
32	Write gate	In
21	Write precomp. enable	In
27	Early clock 2	In
26	Early clock 1	In
25	Normal clock	In
24	Late clock 1	In
23	Late clock 2	In
5	Phase sync.	In
29	AM enable (Address mark enable)	In
40	Reset	In
20	Table sel	In
36	Invert select	In
4	Raw read data	In

Pin No.	Pin name	Input/output
7	D.RD (Delayed read data)	In
14	Sync. in	In
17	Mode sel	In
9	E in sel	In
6	E.RD (E read data)	In
10	L in sel	In
8	L.RD (L head data)	In
15	L3 set	In
16	L4 set	In
30	Write clock	In
35	NRZ read data	Out
19	2-7 write data	Out
39	AM found (Address mark found)	Out
37	Read write clock	Out
28	Early clock out	Out
18	Late write gate	Out
3	Inc out	Out
2	Dec out	Out
43	Sync. read data	Out
13	Sync. detect	Out



Pin Function

2-7 Read Data

The 2-7 Read Data pin inputs the 2-7 code from the disk. The signal synchronized in the data separator is applied to this pin. It must also be synchronized to the VCO Clock from the data separator. When using the internal phase comparator, input the Sync Read Data signal to this pin.

VCO Clock

The VCO Clock is input from a data separator, which has synchronized it with the 2-7 Read Data. The internal phase comparator compares this signal with the Delayed Read Data.

Read Gate

Setting Read Gate input high permits the HD153009 to read data from the disk. It converts the 2-7 code read from the disk into NRZ data for output. Read Gate activates the gain control circuit, performs phase comparison, switches internal circuit clocks, and enables NRZ signal output.

Reference Clock

Reference Clock is the reference clock for this IC. It is also the write data clock. Its frequency must be twice the data transfer rate.

NRZ Write Data

NRZ Write Data inputs NRZ data to be written to the disk. It must be input synchronously with the Write Clock signal when E In Sel and L In Sel pins are set low. Otherwise it must be set synchronously with the Read Write Clock. The polarity of this signal can be switched by the Invert Select pin. Invert Select high selects inverted input and Invert Select low selects noninverted input for 2-7 conversion.

Write Gate

Write Gate high allows data write; NRZ data to be written to the disk is converted to 2-7 code for output. Set Write Gate high for soft-sector address mark write and low for address detection.

Write Precomp. Enable

Setting Write Precomp. Enable low enables write precompensation during writes. In this case, provide a write precompensation clock signal.

Early Clock 2

The phase of the Early Clock 2 write precompensation clock input must lead the Normal Clock.

Early Clock 1

The phase of the Early Clock 1 write precompensation clock input must lead the Normal Clock and follow Early Clock 2.

Normal Clock

The Normal Clock input is used for write precompensation.

Late Clock 1

Late Clock 1 input is used for write precompensation according to write precompensation table 2. Its phase must follow the Normal Clock signal.

Late Clock 2

The Late Clock 1 write precompensation input must follow the Normal Clock and lead Late Clock 1.

Phase Sync

Setting Phase Sync low at the beginning of a read allows 2-7 read data phase to be synchronized in 4T (1000) SYNC pattern (the phase comparator is placed in frequency/phase comparison mode). After synchronization, Phase Sync must be set high for normal decoding. Normally, input Sync Det. to this pin.

AM Enable (Address Mark Enable)

Setting AM Enable input high allows soft-sector address mark write and detection. During address mark write, DC erase continues while AM Enable and Write Gate are held high. If an address mark is detected, the AM Found signal is output at the completion of DC erase, which continues for at least 30 Reference Clock periods. When the AM Found signal is output, the disk controller must clear Address Mark Enable.



Reset

A low-level Reset input initializes the internal circuits at power on. Hold Reset high for normal operation.

Table Sel

Table Sel input high selects write precompensation table 1, and Table Sel input low selects write precompensation table 2.

Invert Select

Invert Select input switches the NRZ polarity for the interface with the controller. When Invert Select is high, the NRZ signal is inverted. When Invert Select is low, the NRZ signal input/output is noninverted.

Raw Read Data

Raw Read Data inputs the 2-7 code read from the disk before it is synchronized in the separator. It is input to the internal comparator for the PLL.

D. RD (Delayed Read Data)

D. RD input is delayed by a period of half the NRZ data transfer rate from the Raw Read Data. It is delivered to the internal comparator for the PLL.

Sync. In

Sync. In input goes to the sync field detect gain control circuit. When the gain control circuit is in normal mode, input the Read Gate signal to Sync. In. When it is in frequency verify mode, input the one-shot output activated by the Raw Read Data signal.

Mode Sel

Mode Sel input selects the mode of the sync field detect gain control circuit. Mode Sel low specifies normal mode, and Mode Sel high specifies frequency verify mode.

E In Sel

E In Sel input low inputs the E. RD signal instead of the D. RD signal into the internal phase comparator for the PLL. When E In Sel and L In Sel are low, the NRZ Write Data signal is synchronized with the Write Clock.

E. RD (E Read Data)

When E In Sel input is low, input the E. RD signal instead of the D. RD signal into the internal phase comparator for the PLL.

L In Sel

Setting the L In Sel input low inputs the L. RD signal instead of the D. RD signal into the internal phase comparator for the PLL. When E In Sel and L In Sel are low, the NRZ Write Data signal is synchronized with the Write Clock.

L. RD (L Read Data)

When L In Sel input is low, input the L. RD signal instead of the D. RD signal into the internal phase comparator for the PLL.

L3 Set, L4 Set

L3 Set and L4 Set input specify the Sync. Detect output period for the sync field detection gain control circuit (table 1.).

Write Clock

Write Clock input enables the NRZ Write Data signal. It is valid while both E In Sel and L In Sel are kept low.

NRZ Read Data

NRZ Read Data outputs the NRZ signal converted from a 2-7 code read from the disk. This signal is synchronous with the Read Write Clock. The polarity can be switched by the Invert Select pin. Invert Select high selects inverted output, and Invert Select low specifies noninverted output.

2-7 Write Data

2-7 Write Data outputs 2-7 codes converted from NRZ signals to write to disk.

AM Found (Address Mark Found)

AM Found goes high when the HD153009 detects an address mark in a soft sector. It is valid only when AM Enable is high.

Table 2 Output Period

L3 Set	L4 Set	Period
High	High	6 Bytes
	Low	2 Bytes
Low	High	4 Bytes
	Low	4 Bytes

**Table 3 NRZ Signal to from
2-7 Code Conversion**

NRZ Code	NRZ Code	2-7 Code
0 1	1 0	0 1 0 0
1 0 1	0 1 0	1 0 0 1 0 0
1 1 0 1	0 0 1 0	0 0 1 0 0 1 0 0
0 0	1 1	1 0 0 0
1 0 0	0 1 1	0 0 1 0 0 0
1 1 0 0	0 0 1 1	0 0 0 0 1 0 0 0
1 1 1	0 0 0	0 0 0 1 0 0

Read Write Clock

For data read, Read Write Clock outputs a clock signal synchronous to the converted NRZ signal. For data write, it outputs a clock signal divided by the Reference Clock signal. The disk controller must enable NRZ Read Data (for reads) and NRZ Write Data (for writes) synchronously with Read Write Clock.

Early Clock Out

Connect the Early Clock Out write precompensation reference clock output directly to the Early Clock 2 pin.

Late Write Gate

The rising edge of the Late Write Gate signal is delayed about 32 Reference Clock periods from the start of writing. During Late Write Gate output, the 2-7 Write Data signal is output normally.

Inc Out

The Inc Out internal comparator signal is output when Read Data phase leads the VCO Clock phase. This signal is passed to the PLL charge pump.

Dec Out

The Dec Out internal comparator signal is output when Read Data phase follows the VCO Clock phase. This signal is passed to the PLL charge pump.

Sync. Read Data

Sync. Read Data outputs the 2-7 Read Data signal phase-synchronized with the PLL, which was synchronized to the VCO Clock signal. It is provided to the 2-7 Read Data pin for 2-7 reverse conversion.

Sync. Detect

The Sync. Detect sync field detect gain control circuit output is normally sent to the Phase Sync. pin. While Sync. Detect is output, the voltage can be quickly stabilized to the PLL voltage by increasing the PLL gain.

Vcc, GND

Vcc supplies the +5 V power. Both Vcc pins must be connected to the power line. All four GND ground pins must be directly grounded separately from each other.



Functional Description**NRZ Signal to 2-7 Code Conversion**

The NRZ write signal is converted into a 2-7 code to be written to the disk. Either the $\overline{\text{NRZ}}$ or NRZ signal is selected depending on the Invert Select pin input level; a high level Invert Select the $\overline{\text{NRZ}}$ signal and a low level selects NRZ. The NRZ write signal is synchronized with the Read Reference Clock signal and then converted into a 2-7 code according to the conversion Table 2. The resulting 2-7 code is subject to write precompensation.

2-7 Code to NRZ Signal Conversion

The 2-7 code read from the disk is converted into an NRZ signal; $\overline{\text{NRZ}}$ or NRZ signal is also selected by the Invert Select signal. The 2-7 code is synchronized with the VCO Clock signal and then converted into an NRZ signal based on the conversion table. The NRZ read signal is synchronized with the read clock signal.

Write Precompensation

The converted 2-7 write code (Figure 1) is subject to write precompensation according to Table 3 or 4.

Table Sel pin chooses either write precompensation table 1 (high level) or write precompensation table 2 (low level).

The amount of write precompensation is determined by the phase of the externally supplied clock signal.

When the Write Precomp. Enable is high level and the Table Sel is high level, the HD153013 activates write-precompensation in table 1 by the built-in delay, and in the other hand, the HD153009 does not activate write-precompensation. (Refer to Table 5)

When the Write Precomp. Enable is high level and the Table Sel is low level, the HD153009 activates write-precompensation in table 2 by the built-in delay, and in the other hand, the HD153013 does not activate write-precompensation. (Refer to Table 5)

Phase Synchronization in 4T (1000) SYNC Pattern

When data is being read from a magnetic disk, the clock phase can be synchronized in 4T (1000) SYNC pattern. In this case, for NRZ signal selection, "11 ... 111" data must be in the SYNC field and "00 ... 000" for $\overline{\text{NRZ}}$ signal. During read, the synchronous signal is applied, during which the phase is synchronized.

Address Mark (DC Erase) Generation

The 2-7 write signal change is halted by the address mark generation signal. The address mark continues to be written while the address mark generation signal is applied.

Address Mark (DC Erase) Detection

The AM detection signal is output following the address mark when the 2-7 read signal remains unchanged for a period exceeding 16 bits of data.

Phase Comparison for the Data Separator

This device incorporates a phase comparator for the data separator (HA16658). This comparator compares Raw Read Data and Delayed Read Data with VCO Clock phase to provide phase comparison signal Inc Out or Dec Out as follows:

- When Read Data phase leads the VCO Clock phase, Inc Out is output.
- When Read Data phase follows the VCO Clock phase, Dec Out is output.

When the Phase Sync. pin is set low, frequency as well as phase are compared between the Read Data and VCO Clock signals. Accordingly, this comparator can be effectively used to stabilize the voltage to the PLL in sync field. The Read Data in sync field is assumed to be 4T (1000).

The Phase Sync. pin input can be appropriately delivered from the Sync. Detect signal output by the built-in gain control circuit.

Gain Control Circuit

The gain control circuit outputs the Sync. Detect signal during SYNC field. Using L3 Set and L4 set input pins, the Sync Detect signal output period can be selected from among 2-, 4-, and 6-byte lengths of the NRZ signal (see Table 6).



Table 4 Write Precompensation Table 1

n\m	2	3	4	5	6	7
2	N	E2	E2	E2	E2	E2
3	L2	E1	E1	E1	E1	E1
4	L2	E1	E1	E1	E1	E1
5	L2	E1	E1	E1	E1	E1
6	L2	E1	E1	E1	E1	E1
7	L2	E1	E1	E1	E1	E1

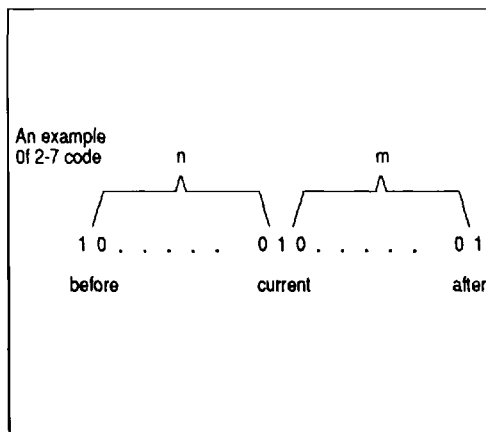
Table 5 Write Precompensation Table 2

n\m	2	3	4	5	6	7
2	N	E1	E2	E2	E2	E2
3	L1	N	E1	E1	E1	E1
4	L2	L1	N	N	E1	E1
5	L2	L1	N	N	N	N
6	L2	L1	L1	N	N	N
7	L2	L1	L1	N	N	N

Note: N: Normal Clock, L2: Late Clock 2, L1: Late Clock 1, E2: Early Clock 2, E1: Early Clock 1, $|L2| > |L1|$, $|E2| > |E1|$

Table 6 Selection of Precompensation Mode

		Write Precompensation Table Select		Precompensation Method	
		HD153009	HD153013	HD153009	HD153013
Write Precomp. Enable Table Sel		HD153009	HD153013	HD153009	HD153013
L	H	1	1	External delay element	External delay element
L	L	2	2	External delay element	External delay element
H	H	—	1	No precompensation	Built-in delay
H	L	2	—	Built-in delay	No precompensation


Figure 1 2-7 Code Example
Table 7 Selection of Sync Detect Period

L3 set	High	High	Low	Low
L4 set	High	Low	High	Low
Sync detect period	6 Bytes	2 Bytes	4 Bytes	4 Bytes

HD153009, HD153013

This circuit has two modes switched via the Mode Sel pin: normal mode (Mode Sel at high) and frequency verification mode (Mode Sel at low).

Normal mode: The Read Gate signal from the controller must be input to the Sync In pin. Immediately after the rising edge of the Read Gate signal, the Sync. Detect signal is set to low during the period specified by the L3 Set and L4 Set pins.

Frequency verification mode: 1 shot output activated by the Raw Read Data signal must be provided to the Sync In pin. If the 1 shot output is

not held low during a 2-bytes NRZ signal after the falling Read Gate signal, the Sync. Detect signal must be set to low. The Sync. Detect signal output period is specified by L3 Set and L4 Set pins.

The Sync. Detect signal must be applied to the Phase Sync. pin of this IC to enable the phase comparator to compare phases and frequencies and to synchronize the phase for read. By providing the Sync. Detect signal to the HA16658's GS pin, PLL gain can be increased.

Table 8 Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
Supply voltage	Vcc	7	V
Input voltage	Vi	5.5	V
Output voltage	Vo	5.5	V
Power consumption	Pc	460	mW
Operating temperature	Topr	-20 to +75	°C
Storage temperature	Tstg	-65 to +150	°C

The absolute maximum ratings are limiting values, to be applied individually, beyond which the device may be permanently damaged. Functional operation under any of these conditions is not guaranteed. Exposing a circuit to its absolute maximum rating for extended periods of time may affect the device's reliability.

Table 9 Electrical Characteristics

Table 9-1 DC Characteristics (Ta=20 to +75°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Supply voltage	Vcc	4.75	5.0	5.25	V	
Input high level voltage	VIH	2.0			V	
Input low level voltage	VIL			0.8	V	
High level input current	IiH			20	μA	Vcc = 5.25 V, Vi = 2.7 V
Low level input current	IiL			-400	μA	Vcc = 5.25 V, Vi = 0.4 V
Output high level voltage	VOH	2.7			V	Vcc = 4.75 V, IOH = 400 μA
Output low level voltage	VOL			0.5	V	Vcc = 4.75 V, IOL = 8 mA
High level output current	IOH			-400	μA	
Low level output current	IOL			8	mA	
Off-state output current	IOZH			20	μA	Vcc = 5.25 V, Vo = 2.7 V
	IOZL			-20	μA	Vcc = 5.25 V, Vo = 0.4 V



Table 9-2 AC Characteristics (T_A = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions	Note
Input clock frequency				30	MHz		Reference /VCO clock
Data transfer rate				15	Mbps		
Reset time	trs	50			ns	Fig. 2	
2-7 read data set-up time	tsr	15			ns	Fig. 3	
2-7 read data hold time	t _{HR}	10			ns	Fig. 3	
NRZ read data set-up time	tsnr	45			ns	Fig. 4 at 10 Mbps	
NRZ read data hold time	t _{HNr}	35			ns	Fig. 4 at 10 Mbps	
Decode time	tDD		7		VCO clock	Fig. 5	
Phase sync. time	tps			3	2-7 Read data pulse	Fig. 6	
Early clock out to precomp. clock TLWP				30	ns	Fig. 7	
Read data delay	TDPC		25		ns	Fig. 8 at 10 Mbps	
Sync. read data set-up time	tSSR	15			ns	Fig. 9	
Sync. read data hold time	tHSR	10			ns	Fig. 9	
Write clock to read clock	tWTR			5	VCO clock	Fig. 10 VCO clock period = Reference clock period	
Read clock to write clock	tRTW			5	Ref. clock	Fig. 10 VCO clock period = Reference clock period	
NRZ write data set-up time	tsnw	10			ns	Fig. 11	
NRZ write data hold time	t _{HNW}	10			ns	Fig. 11	
Encode time	tED		7		Ref. clock	Fig. 12 No write precomp.	
			16		Ref. clock	Fig. 12 With write precomp.	
Write gate to late write Gate (high)	TLWG	30		32	Ref. clock	Fig. 13	
Write gate to late write Gate (low)	TRWG			20	ns	Fig. 13	
Address mark write enable time	tAML			2	Ref. clock	Fig. 14	
Address mark write disable time	tAMH			2	Ref. clock	Fig. 14	
Address mark detect time	tAMR	30			Ref. clock	Fig. 15	
Address mark detect rise time	tAFH			30	ns	Fig. 15	
Address mark detect fall time	tAFL			30	ns	Fig. 15	
Sync detect fall time	tSDD			40	ns	Fig. 16	
Sync. detect time (normal mode)	tsDT		17		Raw read data	Fig. 16 at 4 bytes	
Sync. detect fall time	tSDD		8		Raw read data	Fig. 17	
Sync. detect time (frequency verification mode)	tsDT		17		Raw read data	Fig. 17 at 4 bytes	



HD153009, HD153013

AC Characteristics (Ta=25°C) (cont)

Internal delay E1	t_{E2}	-7	ns	Delay with respect to normal clock
Internal delay E2	t_{E1}	-4	ns	
Internal delay L1	t_{L2}	4	ns	
Internal delay L1	t_{L2}	7	ns	

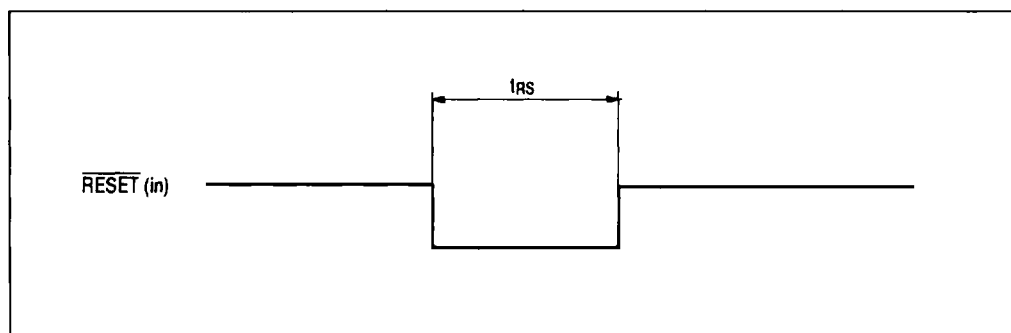


Figure 2 Reset Input

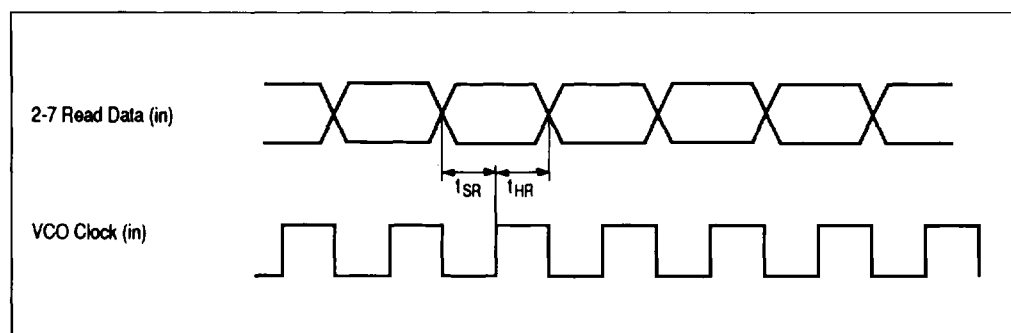


Figure 3 2-7 Read Data

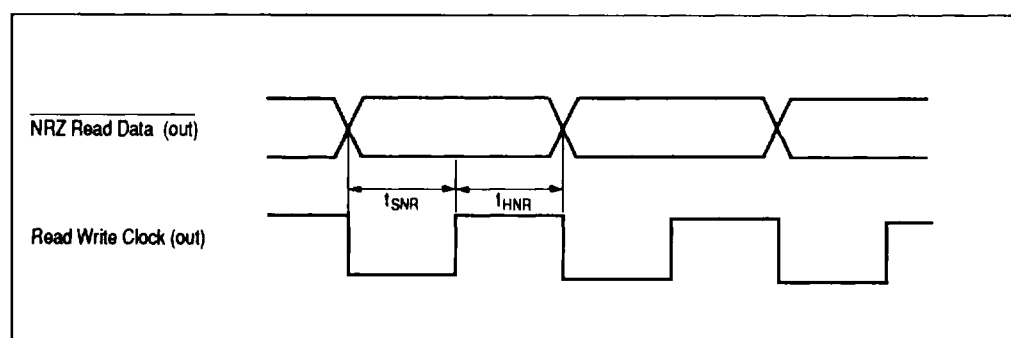


Figure 4 NRZ Read Data



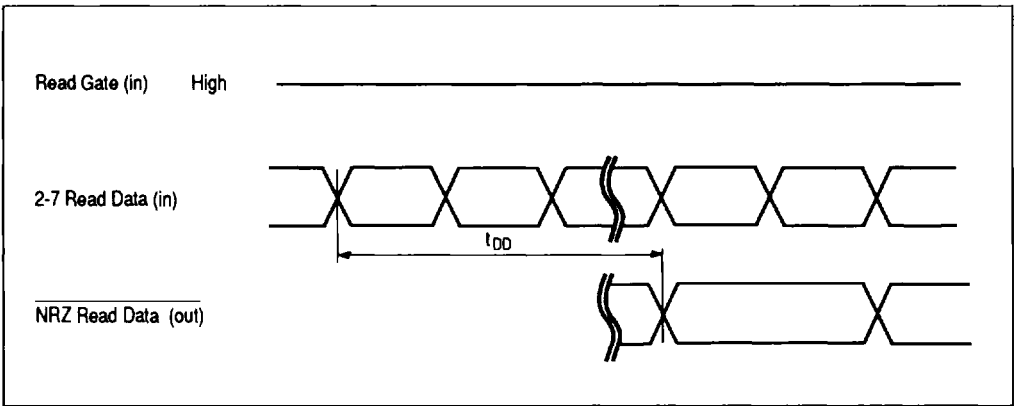


Figure 5 Decode

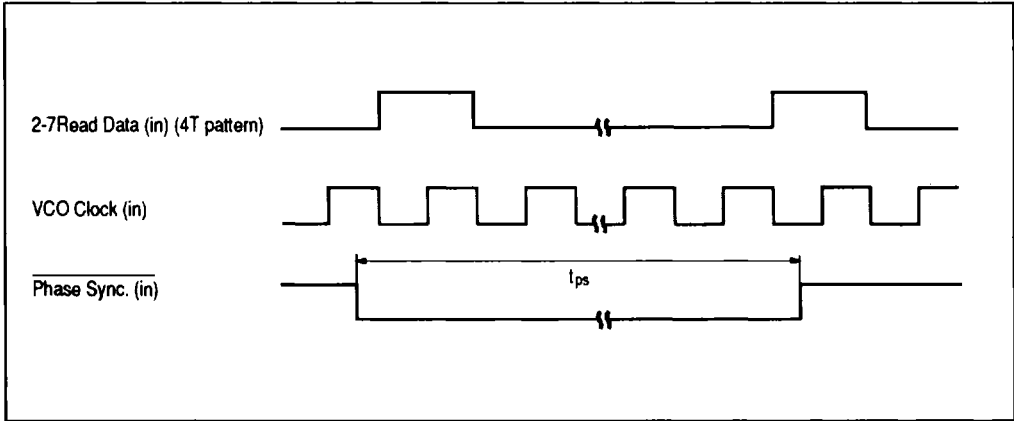


Figure 6 Phase Synchronization

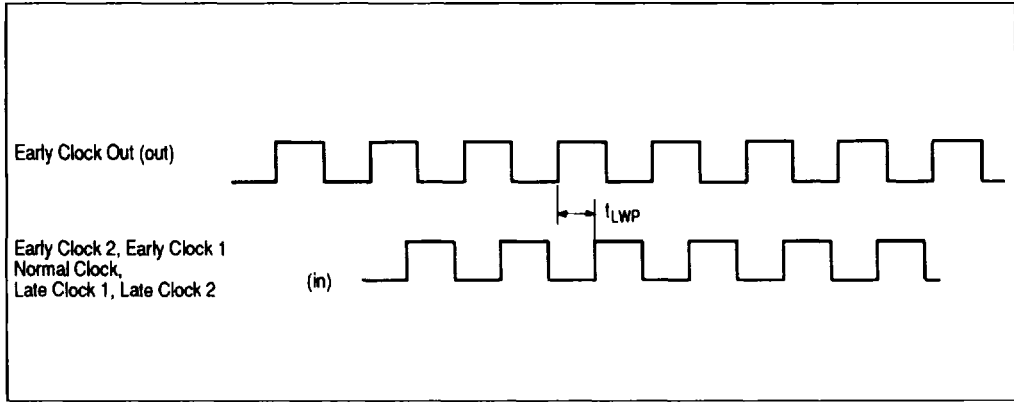


Figure 7 Write Precompensation



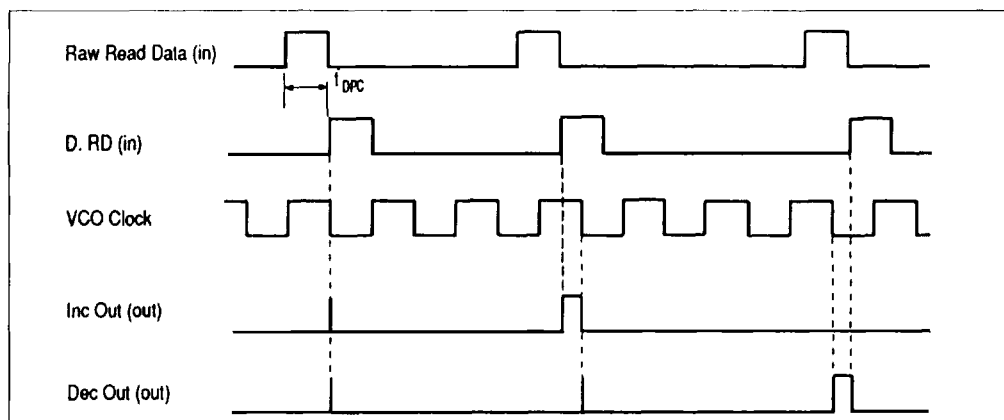


Figure 8 Phase Comparison

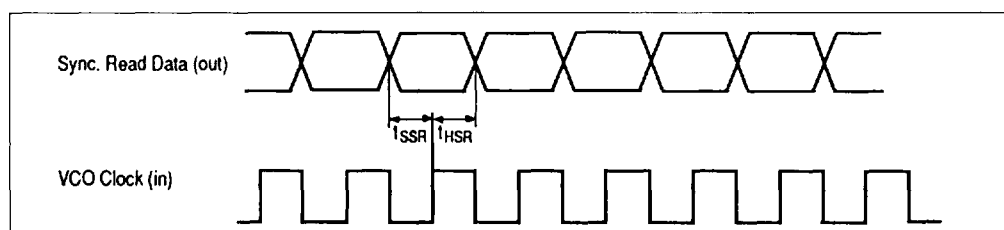


Figure 9 Sync. Read Data

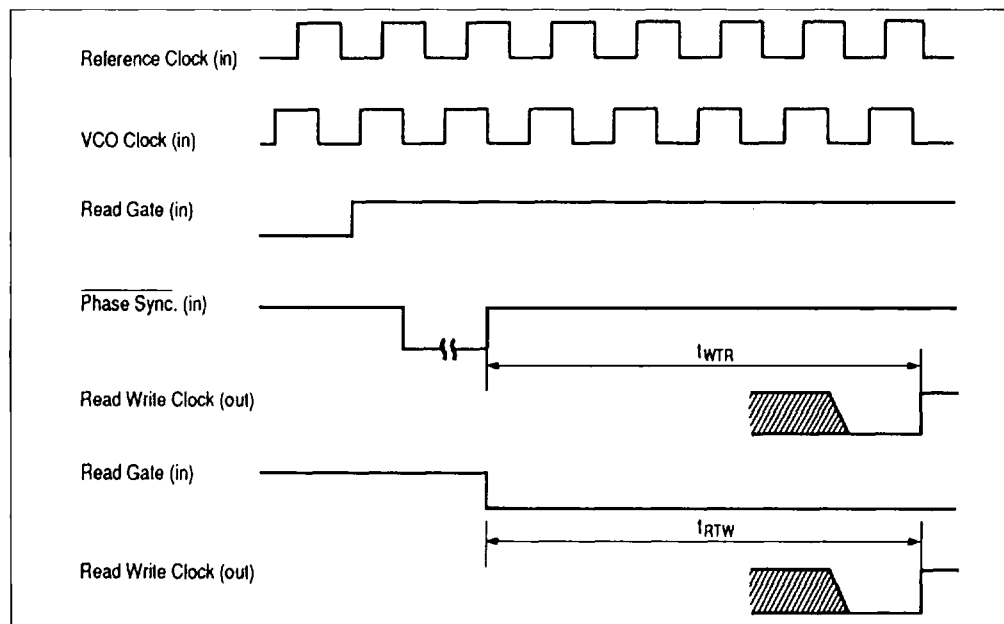


Figure 10 Read Write Clock

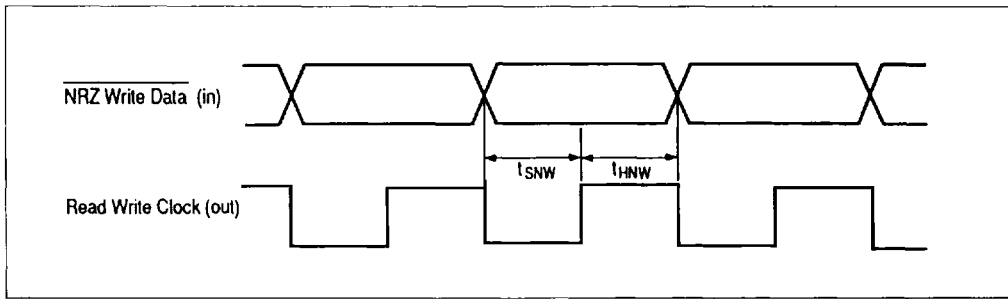


Figure 11 NRZ Write Data Input

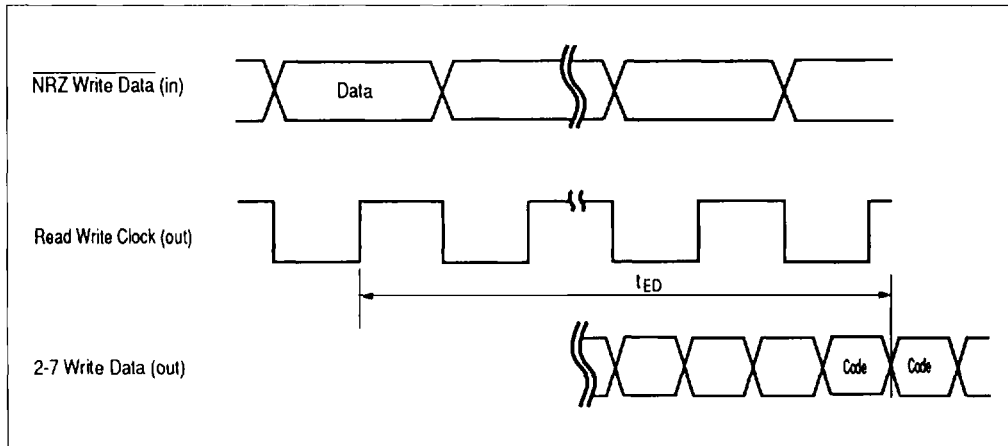


Figure 12 Encode

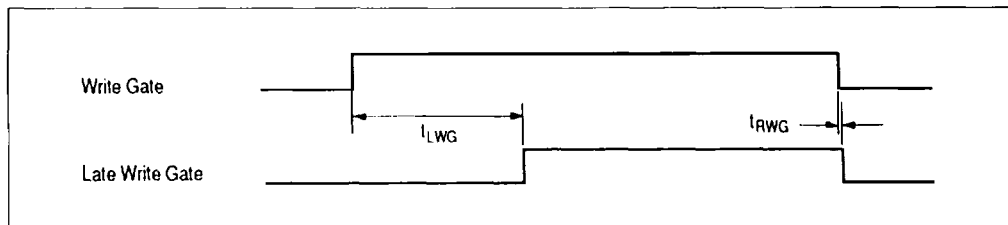


Figure 13 Late Write Gate

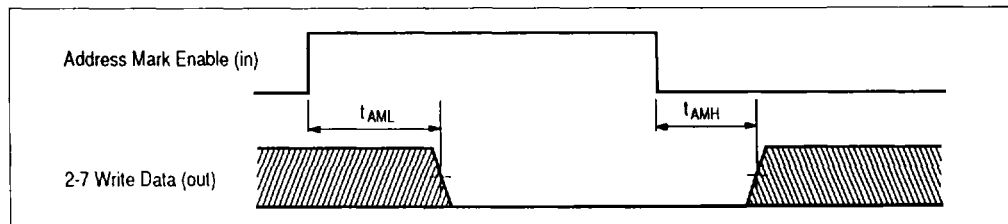


Figure 14 Address Mark Write



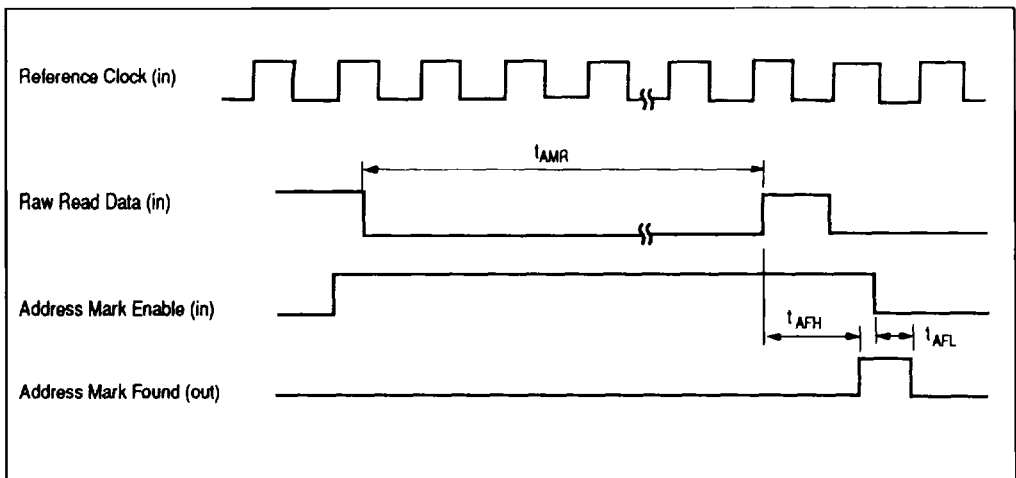


Figure 15 Address Mark Detect

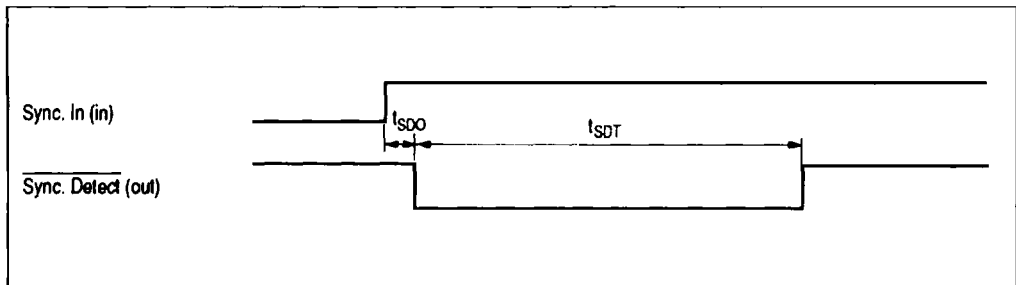


Figure 16 Sync Detect Output(Normal Mode)

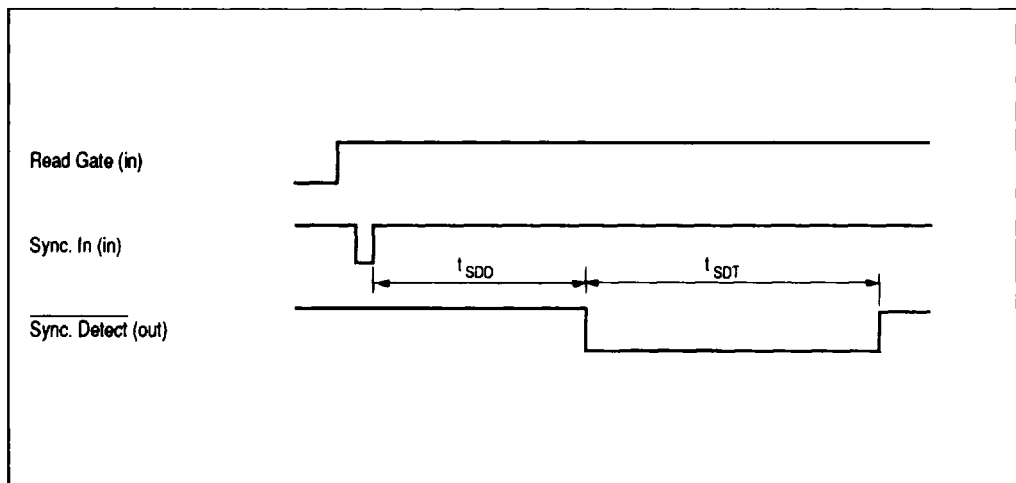


Figure 17 Sync Detect Output(Frequency Verification Mode)



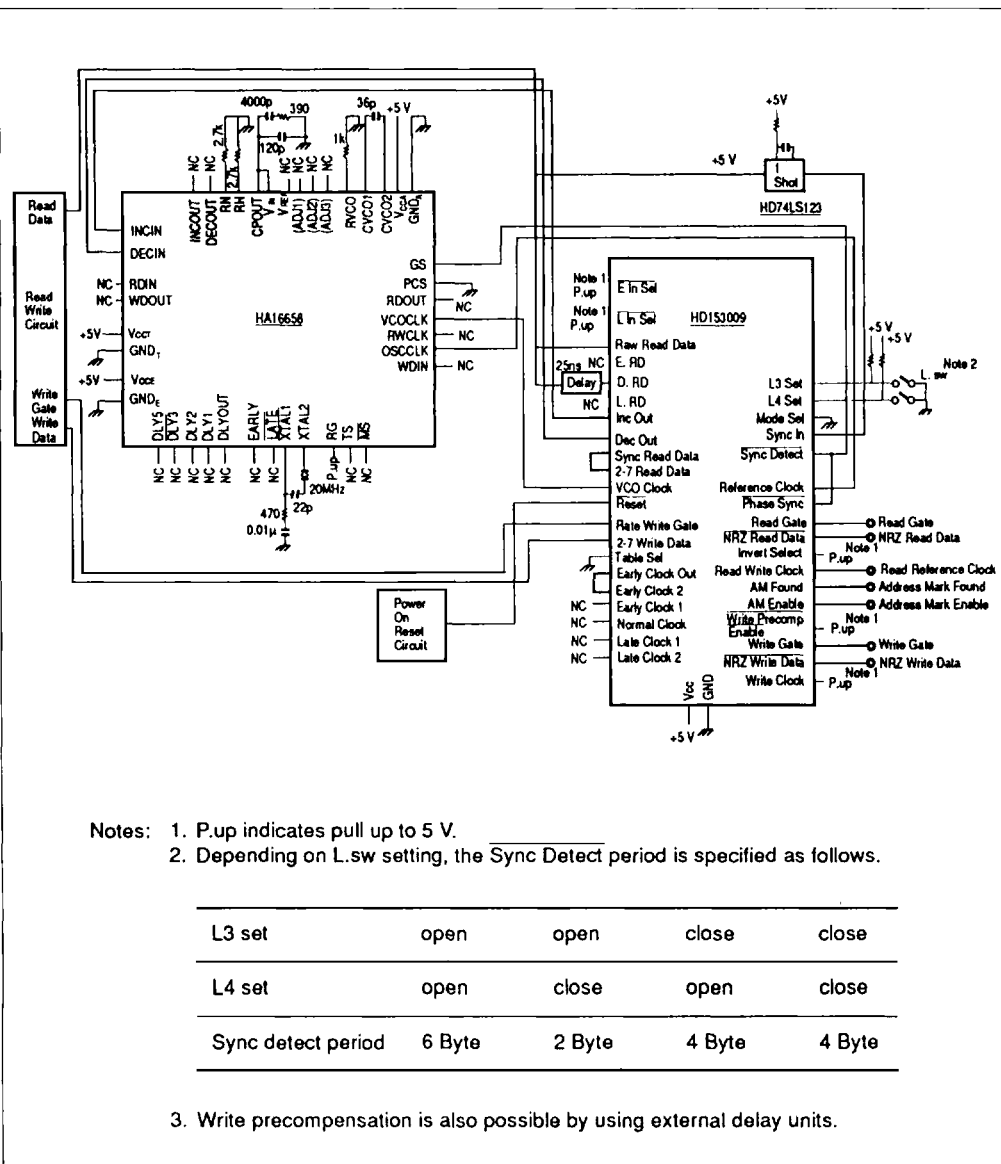


Figure 18 Circuit Example

